

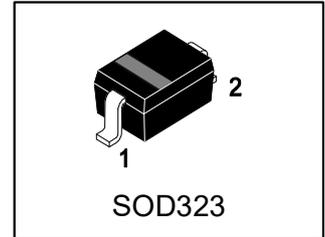
RB751V-40

S-RB751V-40

Schottky Barrier Diode

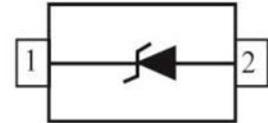
1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low reverse current and low voltage.
- High reliability



2. APPLICATIONS

- Low-power rectification



3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751V-40	5E	3000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak Reverse Voltage	VRM	40	V
DC Reverse Voltage	VR	30	V
Mean Rectifying Current	IO	30	mA
Peak Forward Surge Current	IFSM	200	mA

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	200 1.57	mW mW/°C
Thermal Resistance, Junction-to-Ambient(Note 1)	RθJA	635	°C/W
Junction and Storage temperature	TJ, Tstg	-40 ~ +125	°C

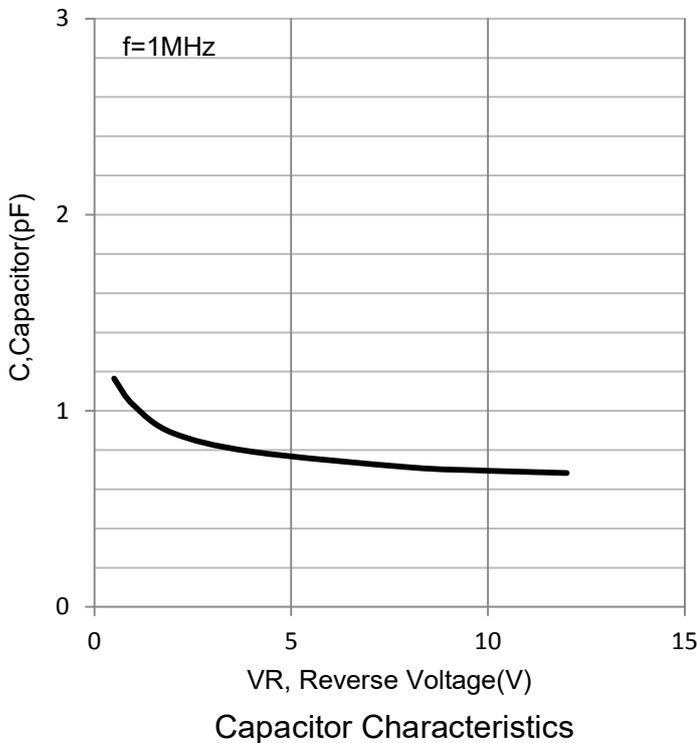
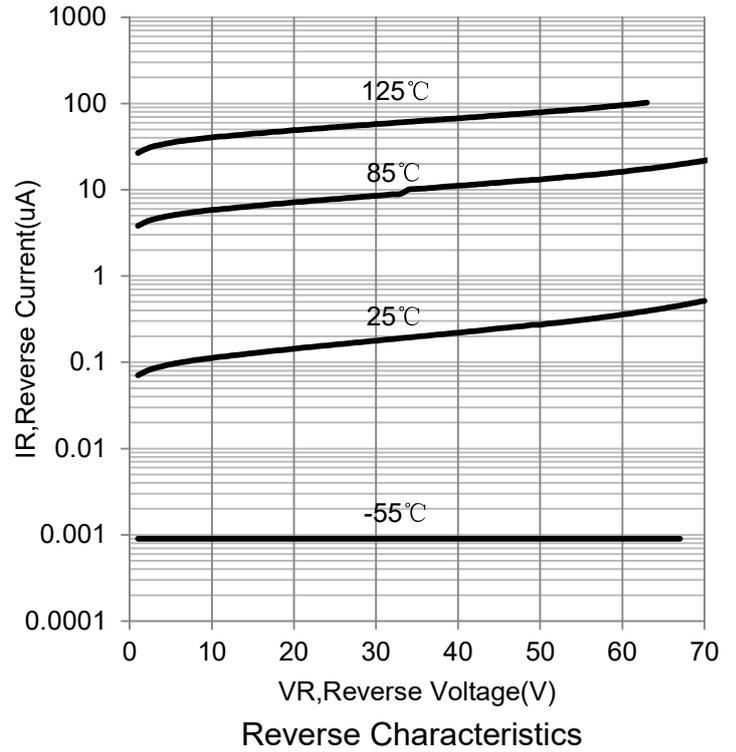
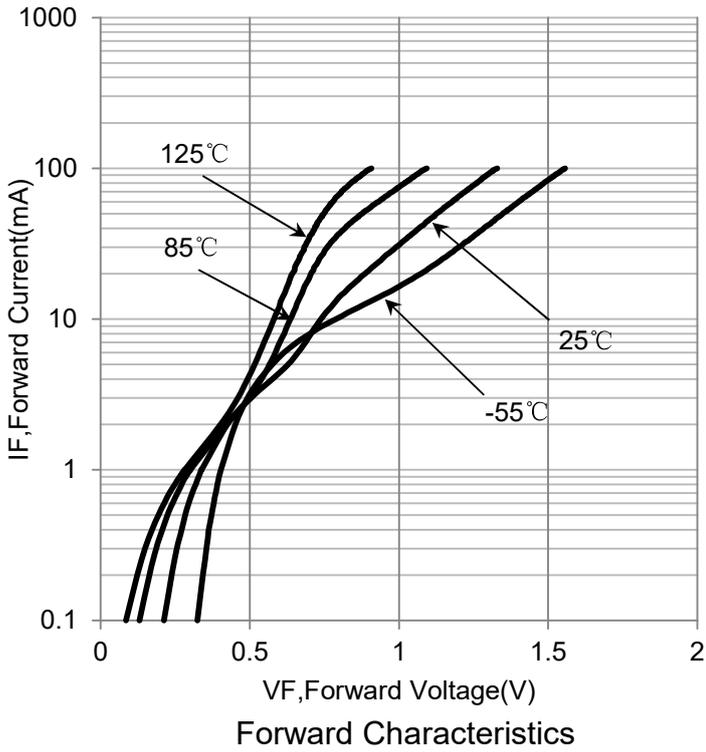
1. FR-5 = 1.0×0.75×0.062 in.

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward voltage(IF=1mA)	VF	-	-	0.37	V
Reverse Current(VR=30V)	IR	-	-	0.5	μA
Diode Capacitance(VR = 1V, f = 1.0 MHz)	CT	-	2	-	pF



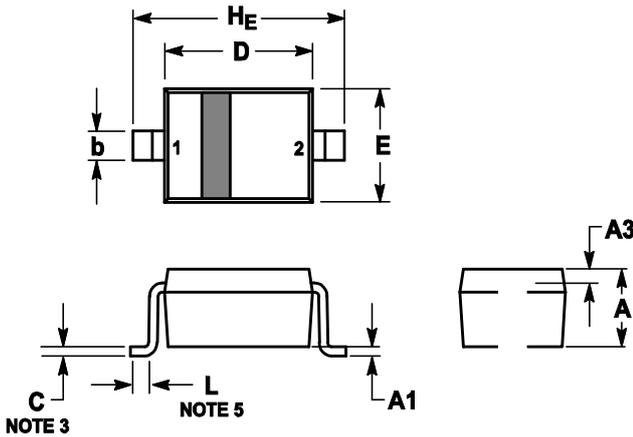
7. ELECTRICAL CHARACTERISTICS CURVES



8. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.8	0.9	1	0.031	0.035	0.04
A1	0	0.05	0.1	0	0.002	0.004
A3	0.15REF			0.006REF		
b	0.25	0.32	0.4	0.01	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.6	1.7	1.8	0.062	0.066	0.07
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H _E	2.3	2.5	2.7	0.09	0.098	0.105

9 SOLDERING FOOTPRINT
